FAIRCHILD SEMICONDUCTOR MPSA12 **NPN Darlington Transistor** • This device is designed for applications requiring extremely high current gain at currents to 1.0A. • Sourced from process 05. • See MPSA14 for characteristics.

TO-92 1. Emitter 2. Base 3. Collector MPSA12

Absolute Maximum Ratings * T_A=25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--|------------|-------|--|
| V _{CES} | Collector-Emitter Voltage | 20 | V | |
| V _{CBO} | Collector-Base Voltage | 20 | V | |
| V _{EBO} | Emitter-Base Voltage | 10 | V | |
| I _C | Collector Current - Continuous | 1.2 | A | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | -55 ~ +150 | °C | |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_A=25°C unless otherwise noted

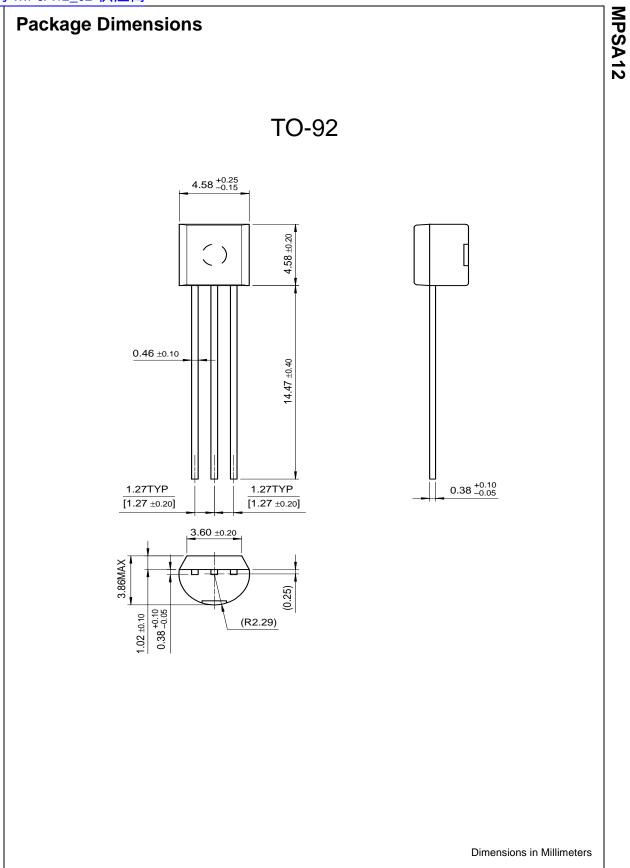
| Parameter | Test Condition | Min. | Тур. | Max. | Units |
|--------------------------------------|--|---|---|---|---|
| cteristics | | | | | |
| Collector-Emitter Breakdown Voltage | $I_{\rm C} = 100 \mu {\rm A}, I_{\rm E} = 0$ | 20 | | | V |
| Collector Cutoff Current | $V_{CB} = 15V, I_E = 0$ | | | 100 | nA |
| Emitter Cutoff Current | $V_{CB} = 15V, I_{C} = 0$ | | | 100 | nA |
| Emitter Cutoff Current | $V_{EB} = 10V, I_{C} = 0$ | | | 100 | nA |
| cteristics * | | | | | |
| DC Current Gain | $V_{CE} = 5.0V, I_{C} = 10mA$ | 20,000 | | | |
| Collector-Emitter Saturation Voltage | $I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0.01 {\rm mA}$ | | | 1.0 | V |
| Base-Emitter On Voltage | I _C = 10mA, V _{CE} = 5.0V | | | 1.4 | V |
| | Collector-Emitter Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current Emitter Cutoff Current Emitter Cutoff Current cteristics * DC Current Gain Collector-Emitter Saturation Voltage | cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ Eteristics *DC Current GainDC Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mACollector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA | cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 20Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA20,000 | cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 20Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 20Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA20 | cteristicsCollector-Emitter Breakdown Voltage $I_C = 100\mu$ A, $I_E = 0$ 20Collector Cutoff Current $V_{CB} = 15$ V, $I_E = 0$ 100Emitter Cutoff Current $V_{CB} = 15$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Emitter Cutoff Current $V_{EB} = 10$ V, $I_C = 0$ 100Current Gain $V_{CE} = 5.0$ V, $I_C = 10$ mA20,000Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 0.01$ mA1.0 |

e Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%

Thermal Characteristics TA=25°C unless otherwise noted

| Symbol | Parameter | Max. | Units |
|-----------------------|---|------|-------|
| P _D | Total Device Dissipation | 625 | mW |
| - | Derate above 25°C | 5.0 | mW/°C |
| $R_{	extsf{	heta}JC}$ | Thermal Resistance, Junction to Case | 83.3 | °C/W |
| $R_{	hetaJA}$ | Thermal Resistance, Junction to Ambient | 200 | °C/W |

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PRODUCT STATUS DEFINITIONS

Definition of Terms

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|--------------------------|---------------------------|---|
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